

SIDC85D170H

Fast switching diode chip in EMCON 3-Technology

FEATURES:

- 1700V EMCON 3 technology 200 µm chip
- soft, fast switching
- low reverse recovery charge
- small temperature coefficient

This chip is used for:

EUPEC power modules



Applications:

• resonant applications, drives

Chip Type	V_R	I _F	Die Size	Package	Ordering Code
SIDC85D170H	1700V	150A	9.2 x 9.2 mm ²	sawn on foil	Q67050-A4178- A001

MECHANICAL PARAMETER:

WILCHANICAL FARAWILTER.			
Raster size	9.2 x 9.2		
Area total / active	84.64 / 67.8		
Anode pad size	7.18 x 7.18		
Thickness	200		
Wafer size	150		
Flat position	180		
Max. possible chips per wafer	160 pcs		
Passivation frontside	Photoimide		
Anode metallization	3200 nm Al Si Cu		
Cathode metallization	Ni Ag –system suitable for epoxy and soft solder die bonding		
Die bond	electrically conductive glue or solder		
Wire bond	AI, ≤500μm		
Reject Ink Dot Size	Ø 0.65mm; max 1.2mm		
Recommended Storage Environment	store in original container, in dry nitrogen, < 6 month at an ambient temperature of 23°C		



SIDC85D170H

Maximum Ratings

Parameter	Symbol	Condition	Value	Unit
Repetitive peak reverse voltage	V_{RRM}		1700	V
Continuous forward current limited by T_{jmax}	I _F		150	
Single pulse forward current (depending on wire bond configuration)	I _{FSM}	$t_P = 10 \text{ ms sinusoidal}$	740	А
Maximum repetitive forward current limited by T _{jmax}	I _{FRM}		300	
Operating junction and storage temperature	$T_{\rm j}$, $T_{ m stg}$		-55+150	°C

Static Electrical Characteristics (tested on chip), T_j =25 °C, unless otherwise specified

Parameter	Symbol	Condi	Value			Unit	
i arameter	Symbol	Conditions		min.	Тур.	max.	
Reverse leakage current	I_{R}	V _R =1700V	<i>T_j</i> =25 °C			27	μΑ
Cathode-Anode breakdown Voltage	V_{Br}	I _R =0.25mA	<i>T_j</i> =25°C	1700			V
Forward voltage drop	V _F	I _F =150A	<i>T_j</i> =25 °C		1.8		V

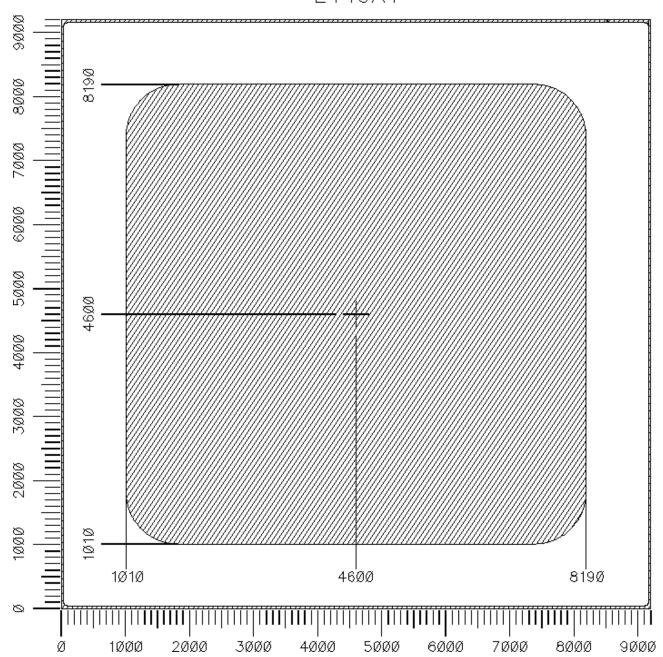
Dynamic Electrical Characteristics, at T_j = 25 °C, unless otherwise specified, tested at component

Parameter	Symbol	Conditions		Value			Unit
raiailletei	Syllibol			min.	Тур.	max.	John
Peak recovery current	I _{RRM1}	I _F =150A di/dt=770A/ m s	$T_j = 25 ^{\circ}C$		131		Α
	I _{RRM2}	$V_R=900V$	$T_j = 125 ^{\circ}\text{C}$		158		
Reverse recovery charge	Q _{rr1}	I _F =150A di/dt=770A/ m s	T _j =25°C		35.8		μC
	Q _{rr2}	$V_R=900V$	T _j =125°C		62.3		μΟ
Peak recovery energy	E _{rec 1}	I _F =150A	T _j =25°C		24.2		
	E _{rec2}	$di/dt=770A/\mathbf{m}s$ $V_R=900V$	T _j =125°C		42.9		mJ



CHIP DRAWING:







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FURTHER ELECTRICAL CHARACTERISTICS:

This chip data sheet refers to the device data sheet	INFINEON TECHNOLOGIES / EUPEC	tbd
Description:		
AQL 0,65 for visual inspection according to	failure catalog	
Electrostatic Discharge Sensitive Device ac	cording to MIL-STD 883	

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